MC14049UB

Hex Buffers

The MC14049UB hex inverter/buffer is constructed with MOS P–channel and N–channel enhancement mode devices in a single monolithic structure. This complementary MOS device finds primary use where low power dissipation and/or high noise immunity is desired. This device provides logic–level conversion using only one supply voltage, V_{DD}. The input–signal high level (V_{IH}) can exceed the V_{DD} supply voltage for logic–level conversions. Two TTL/DTL Loads can be driven when the device is used as CMOS–to–TTL/DTL converters (V_{DD} = 5.0 V, $V_{OL} \leq$ 0.4 V, $I_{OL} \geq$ 3.2 mA). Note that pins 13 and 16 are not connected internally on this device; consequently connections to these terminals will not affect circuit operation.

- High Source and Sink Currents
- High–to–Low Level Converter
- Supply Voltage Range = 3.0 V to 18 V
- Meets JEDEC UB Specifications
- V_{IN} can exceed V_{DD}
- Improved ESD Protection on All Inputs

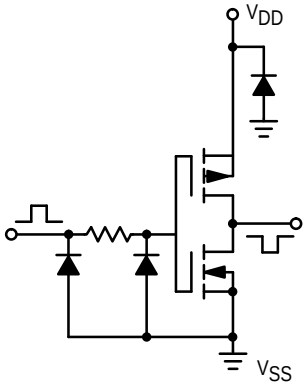
MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

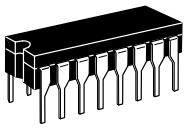
Rating	Symbol	Value	Unit
DC Supply Voltage	V_{DD}	– 0.5 to + 18	V
Input Voltage (DC or Transient)	V_{in}	– 0.5 to + 18	V
Output Voltage (DC or Transient)	V_{out}	– 0.5 to V_{DD} + 0.5	V
Input Current (DC or Transient), per Pin	I_{in}	± 10	mA
Output Current (DC or Transient), per Pin	I_{out}	+ 45	mA
Power Dissipation, per Package† Plastic/Ceramic SOIC	P_D	 825 740	mW
Storage Temperature	T_{stg}	– 65 to + 150	°C
Lead Temperature (8–Second Soldering)	T_L	260	°C

* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating: All Packages: See Figure 4.

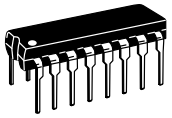
CIRCUIT SCHEMATIC
(1/6 OF CIRCUIT SHOWN)

MC14049UB

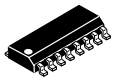




L SUFFIX
CERAMIC
CASE 620



P SUFFIX
PLASTIC
CASE 648



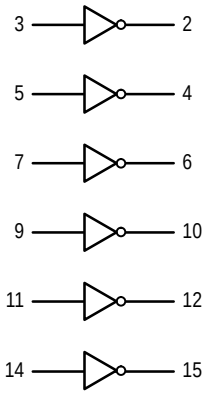
D SUFFIX
SOIC
CASE 751B

ORDERING INFORMATION

MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBD	SOIC

T_A = – 55° to 125°C for all packages.

LOGIC DIAGRAM
MC14049UB



NC = PIN 13, 16
V_{SS} = PIN 8
V_{DD} = PIN 1

REV 3
1/94

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ	25°C Max	125°C Min	125°C Max	Unit
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
"1" Level V_{in} = 0 or V_{DD}	V_{OH}	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage "0" Level	V_{IL}									Vdc
(V_O = 4.5 Vdc)		5.0	—	1.0	—	2.25	1.0	—	1.0	
(V_O = 9.0 Vdc)		10	—	2.0	—	4.50	2.0	—	2.0	
(V_O = 13.5 Vdc)		15	—	2.5	—	6.75	2.5	—	2.5	
"1" Level	V_{IH}									Vdc
(V_O = 0.5 Vdc)		5.0	4.0	—	4.0	2.75	—	4.0	—	
(V_O = 1.0 Vdc)		10	8.0	—	8.0	5.50	—	8.0	—	
(V_O = 1.5 Vdc)		15	12.5	—	12.5	8.25	—	12.5	—	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	– 1.6	—	– 1.25	– 2.5	—	– 1.0	—	
(V_{OH} = 9.5 Vdc)		10	– 1.6	—	– 1.3	– 2.6	—	– 1.0	—	
(V_{OH} = 13.5 Vdc)		15	– 4.7	—	– 3.75	– 10	—	– 3.0	—	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	3.75	—	3.2	6.0	—	2.6	—	mAdc
(V_{OL} = 0.5 Vdc)		10	10	—	8.0	16	—	6.6	—	
(V_{OL} = 1.5 Vdc)		15	30	—	24	40	—	19	—	
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	10	20	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0	—	1.0	—	0.002	1.0	—	30	µAdc
		10	—	2.0	—	0.004	2.0	—	60	
		15	—	4.0	—	0.006	4.0	—	120	
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0	I_T = (1.8 µA/kHz) f + I_{DD}							µAdc
		10	I_T = (3.5 µA/kHz) f + I_{DD}							
		15	I_T = (5.3 µA/kHz) f + I_{DD}							

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

**The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.002.

SWITCHING CHARACTERISTICS* (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ #	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (0.8 ns/pF) C_L + 60 ns		5.0	—	100	160	
t_{TLH} = (0.3 ns/pF) C_L + 35 ns		10	—	50	100	
t_{TLH} = (0.27 ns/pF) C_L + 26.5 ns		15	—	40	60	
Output Fall Time	t_{THL}					ns
t_{THL} = (0.3 ns/pF) C_L + 25 ns		5.0	—	40	60	
t_{THL} = (0.12 ns/pF) C_L + 14 ns		10	—	20	40	
t_{THL} = (0.1 ns/pF) C_L + 10 ns		15	—	15	30	
Propagation Delay Time	t_{PLH}					ns
t_{PLH} = (0.38 ns/pF) C_L + 61 ns		5.0	—	80	120	
t_{PLH} = (0.20 ns/pF) C_L + 30 ns		10	—	40	65	
t_{PLH} = (0.11 ns/pF) C_L + 24.5 ns		15	—	30	50	
Propagation Delay Time	t_{PHL}					ns
t_{PHL} = (0.38 ns/pF) C_L + 11 ns		5.0	—	30	60	
t_{PHL} = (0.12 ns/PF) C_L + 9 ns		10	—	15	30	
t_{PHL} = (0.11 ns/pF) C_L + 4.5 ns		15	—	10	20	

* The formulas given are for the typical characteristics only at 25°C.
#Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

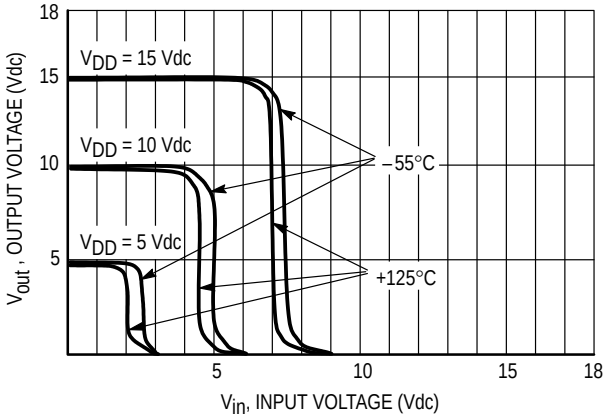


Figure 1. Typical Voltage Transfer Characteristics versus Temperature

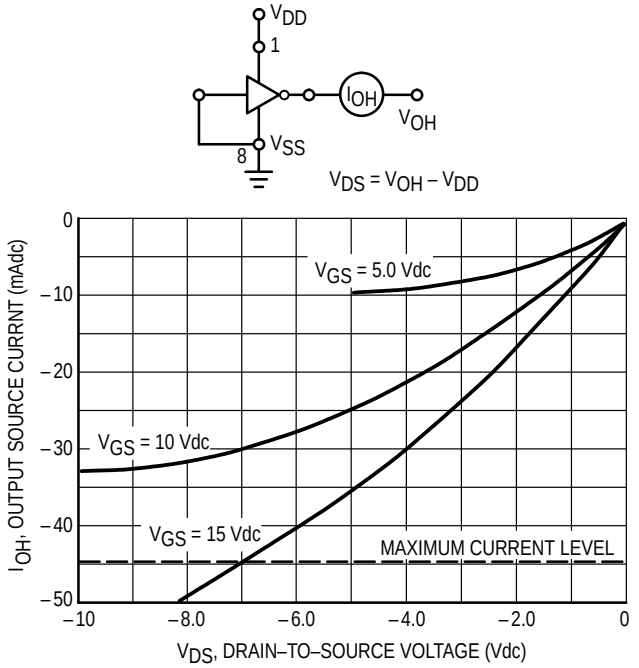


Figure 2. Typical Output Source Characteristics

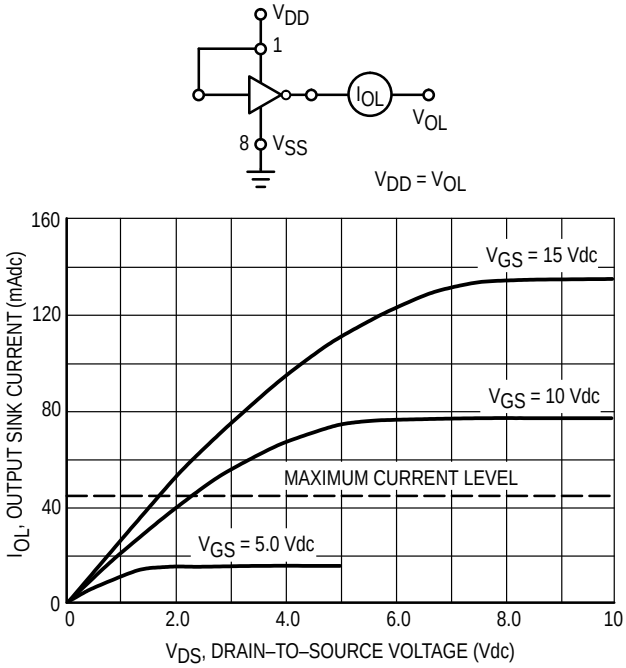


Figure 3. Typical Output Sink Characteristics

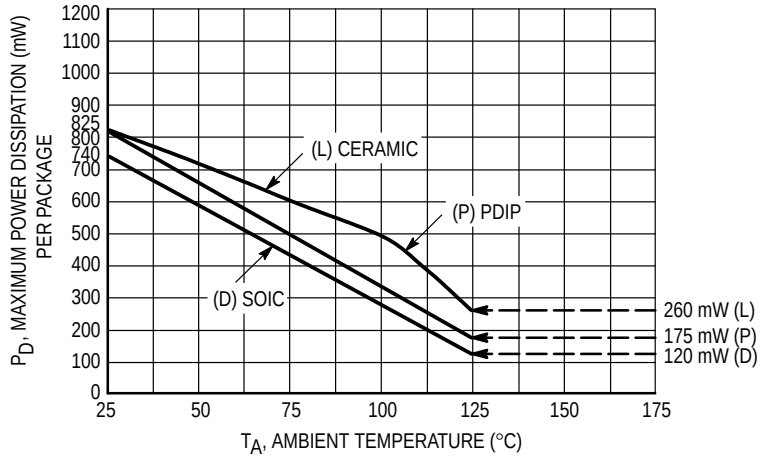


Figure 4. Ambient Temperature Power Derating

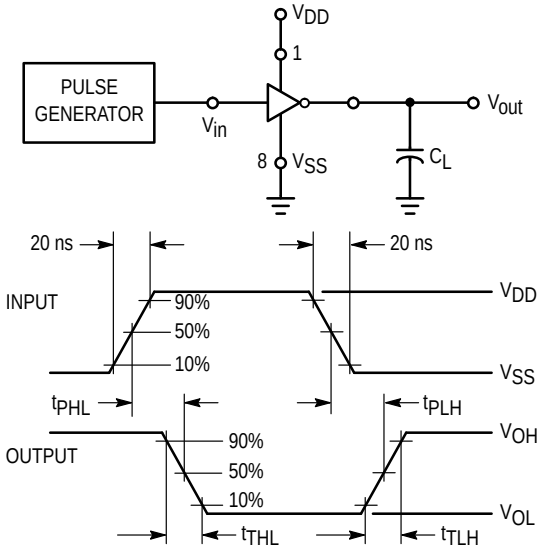
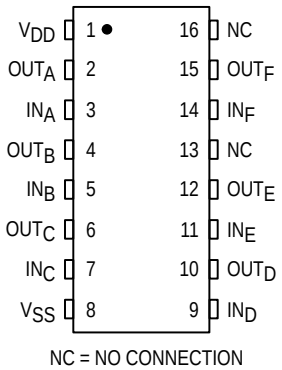


Figure 5. Switching Time Test Circuit and Waveforms

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields referenced to the V_{SS} pin, only. Extra precautions must be taken to avoid applications of any voltage higher than the maximum rated voltages to this high-impedance circuit. For proper operation, the ranges $V_{SS} \le V_{in} \le 18$ V and $V_{SS} \le V_{out} \le V_{DD}$ are recommended.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

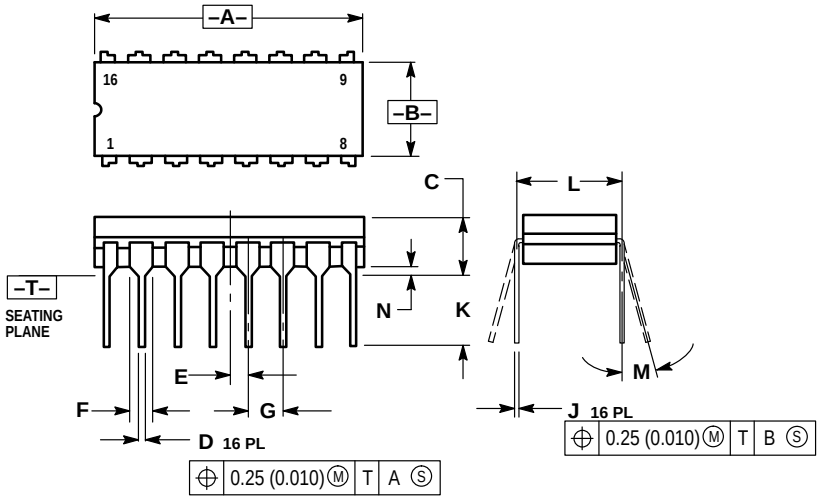
PIN ASSIGNMENT



NC = NO CONNECTION

OUTLINE DIMENSIONS

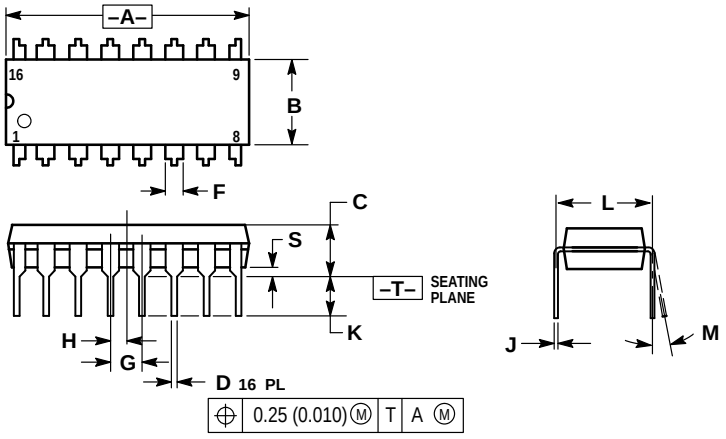
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE V



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.020	0.040	0.51	1.01

P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R

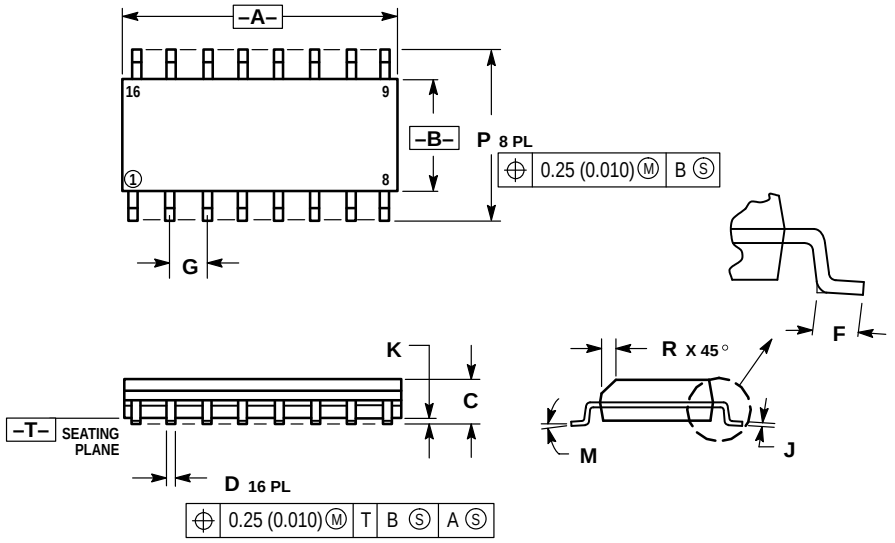


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

OUTLINE DIMENSIONS

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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